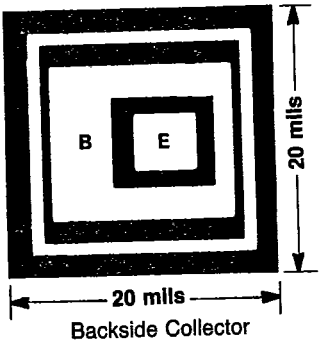
DIE NO. 2C5551 — NPN
LINE SOURCE — DMB106

This die provides performance similar to that of the following device types:

2N4409	MM3008
2N4410	MM3009
2N4418*	MPS5135
2N5550	MPSD02
2N5551	MPSL01

Designed for high-voltage, general-purpose amplifier applications.

*No longer available



Backside Collector

METALLIZATION —
Top ..... Al
Back ..... Au

BACKSIDE GOLD 3000Å

DIE THICKNESS ..... 6 ± 2 mils

BONDING PAD SIZE —
Emitter ..... 4.2 x 4.6 mils
Base ..... 2.8 x 9.0 mils

GLASSIVATION — The die active area, except for bond windows, is covered with Glassivation to protect from contaminants and accidental bonding.

ELECTRICAL CHARACTERISTICS (T_A = 25°C; Note 1)

Parameter	Test Conditions	Min	Max	Unit
BV_{CEO}	I_C = 1.0 mAdc, I_B = 0	160	—	Vdc
BV_{CBO}	I_C = 100 μAdc, I_E = 0	180	—	Vdc
BV_{EBO}	I_E = 10 μAdc, I_C = 0	6.0	—	Vdc
I_{CBO}	V_{CB} = 120 Vdc, I_E = 0	—	50	nAdc
h_{FE}	I_C = 10 mAdc, V_{CE} = 5.0 Vdc	80	250	—

NOTES:
1. Because of the limitations of probe testing, only dc parameters are tested. These parameters must be measured using pulse techniques: pulse width ≤ 300 μs, duty cycle ≤ 2%.
2. Detailed device characteristics are available from your Motorola sales representative.